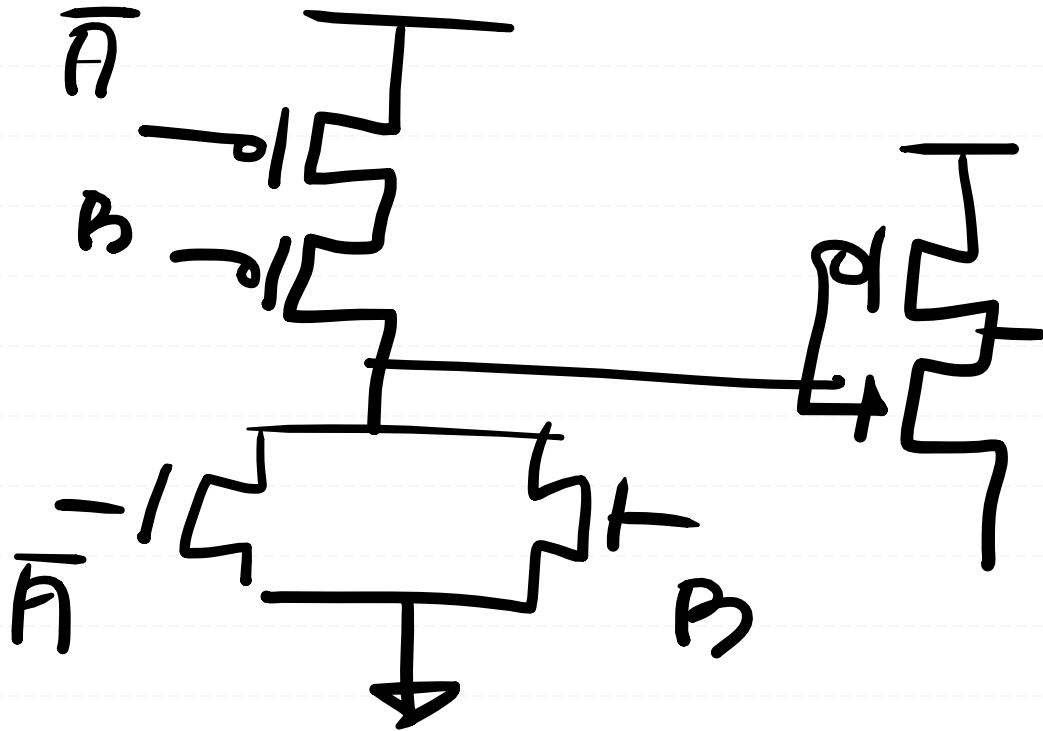
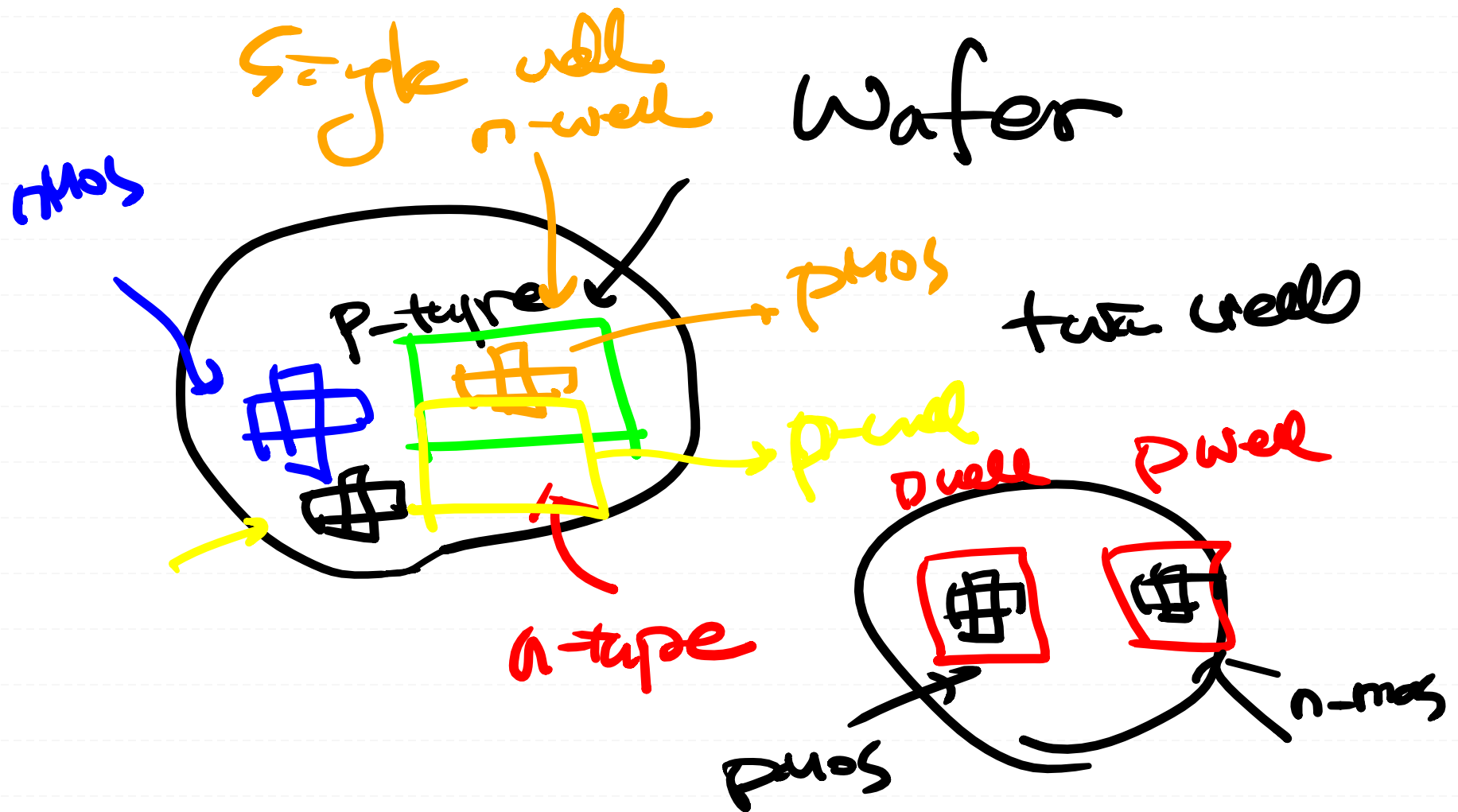


$$F = \bar{A} \quad \square = \text{OR}$$

$$\textcircled{1} F = \bar{A} + B$$

$$= \overline{\bar{\bar{A} + B}}$$





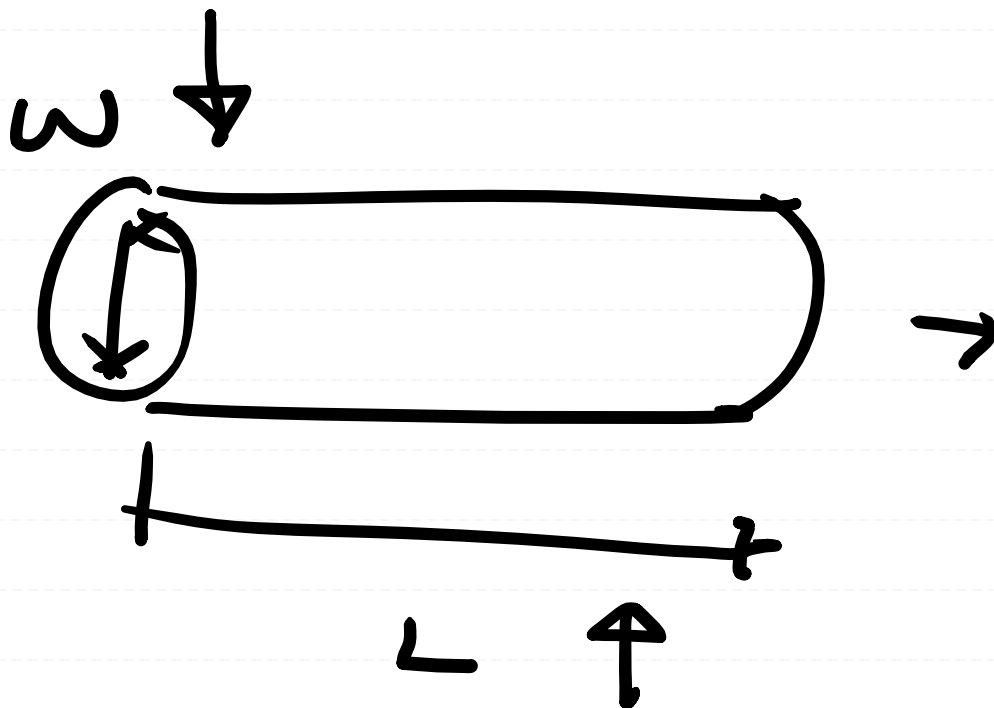
A B C D

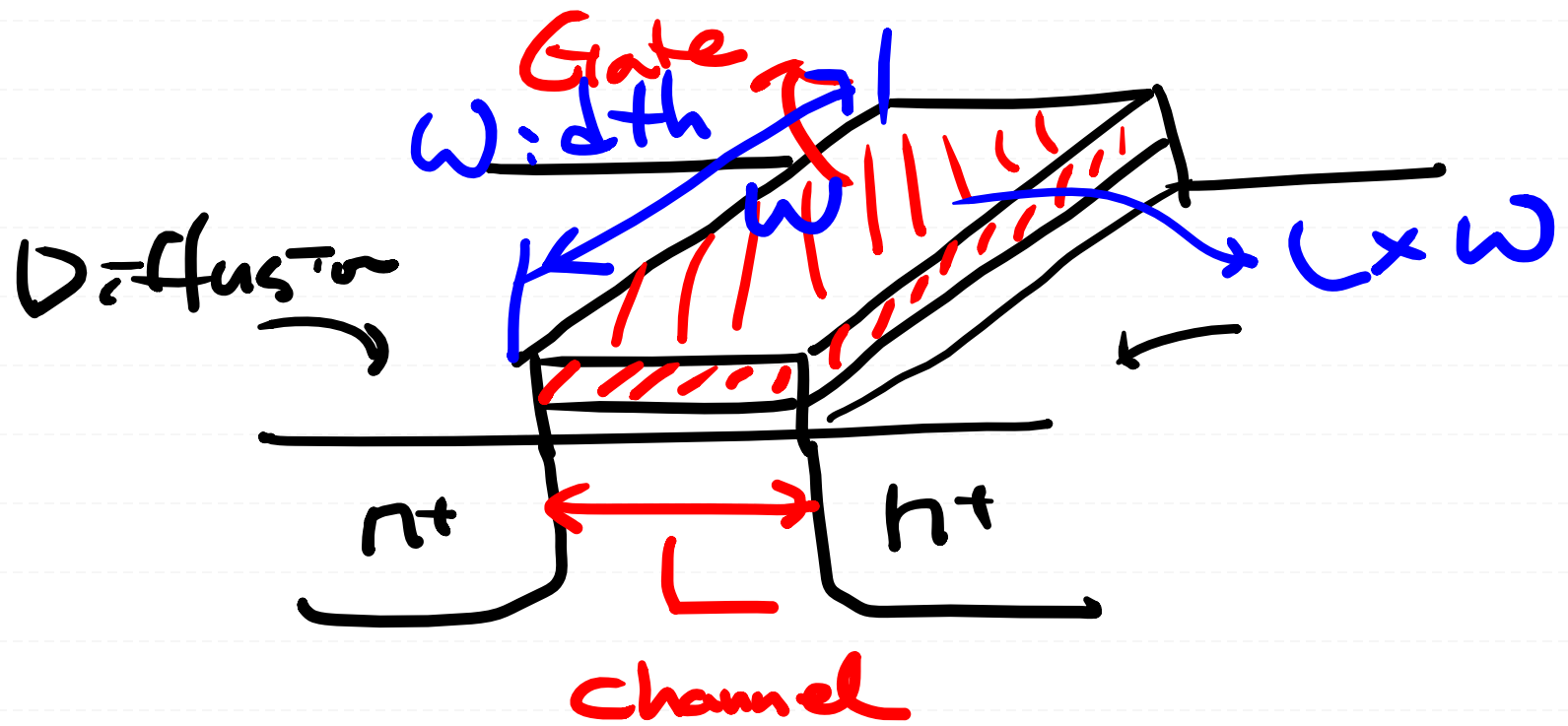
AB

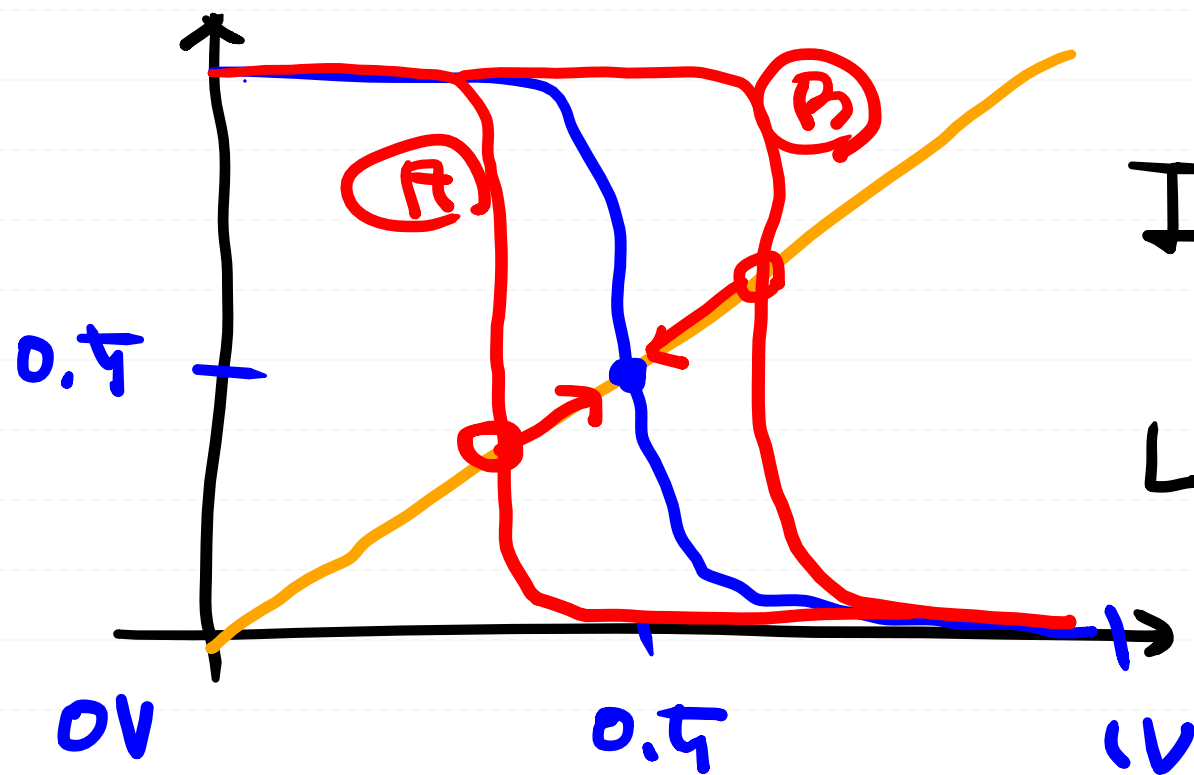
CD	00	01	11	10
00	0	5	13	9
01	1	6	14	10
11	4	8	16	12
10	3	7	15	11


 $I_{Dsat} = \frac{1}{2} \underbrace{\mu_n}_{(1)} \underbrace{C_{ox}}_{(2)} \underbrace{\frac{W}{L}}_{(3)} (V_{gs} \underbrace{- V_{th}}_{(4)})^2$

$I \propto \frac{W}{L}$

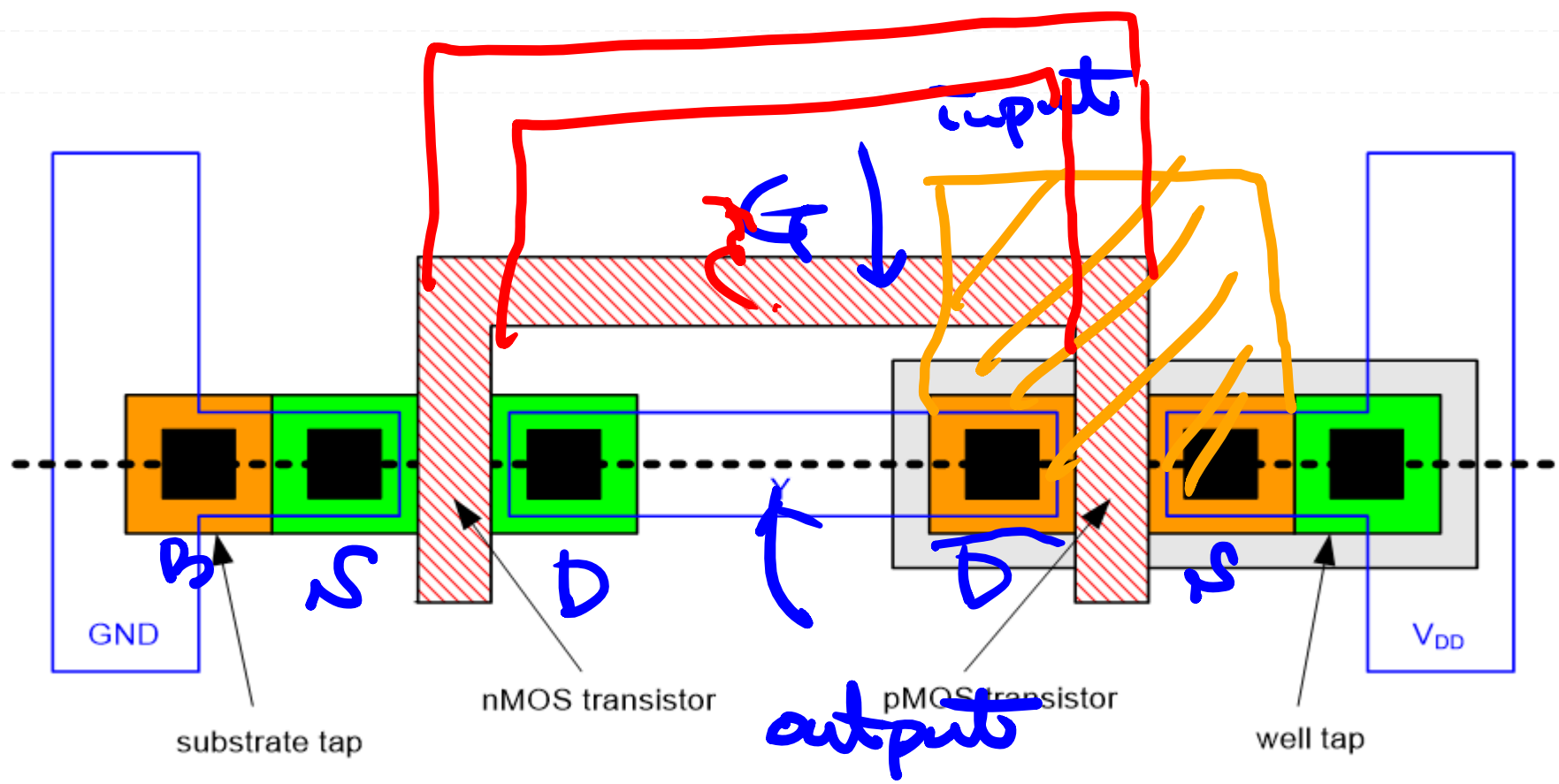


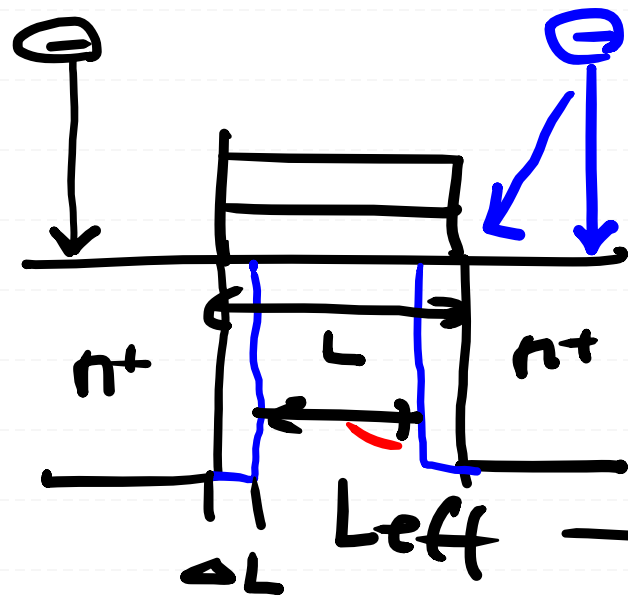




$$I \propto \frac{V}{L}$$

$$L = 35 \text{ nm}$$

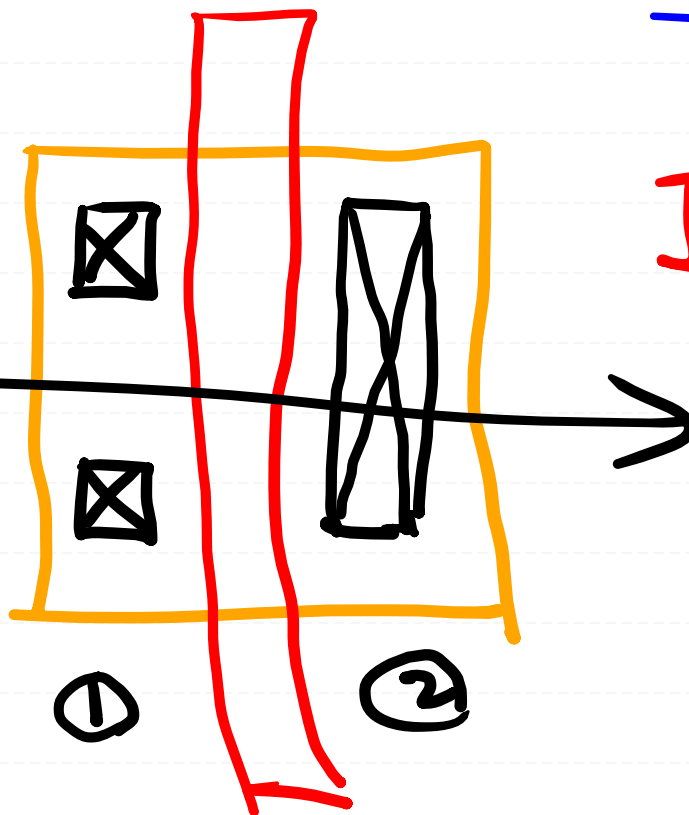




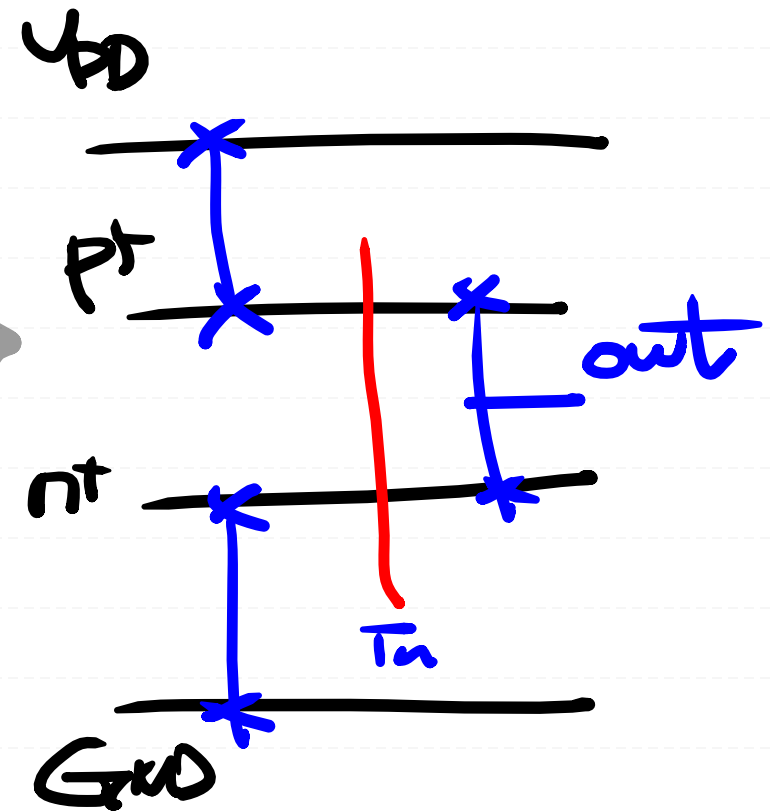
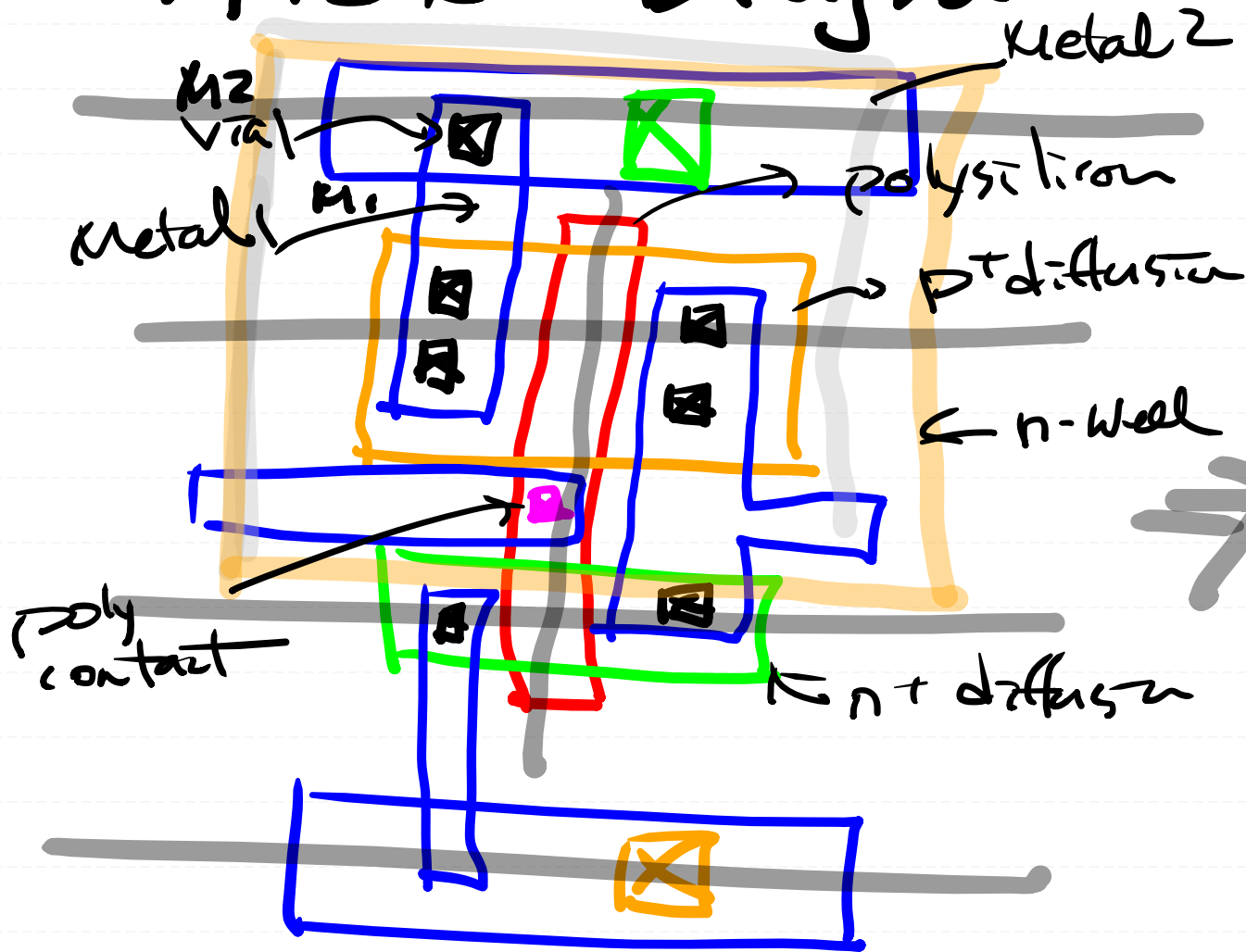
25nm ↓

$I_d \propto \frac{W}{L}$

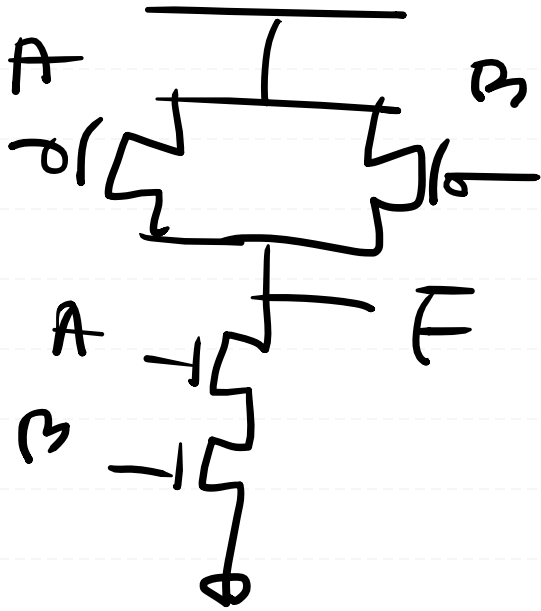
$$L = L_{eff} + 2\Delta L$$



Stick Diagram



2 XNAND $F = \overline{A \cdot B}$


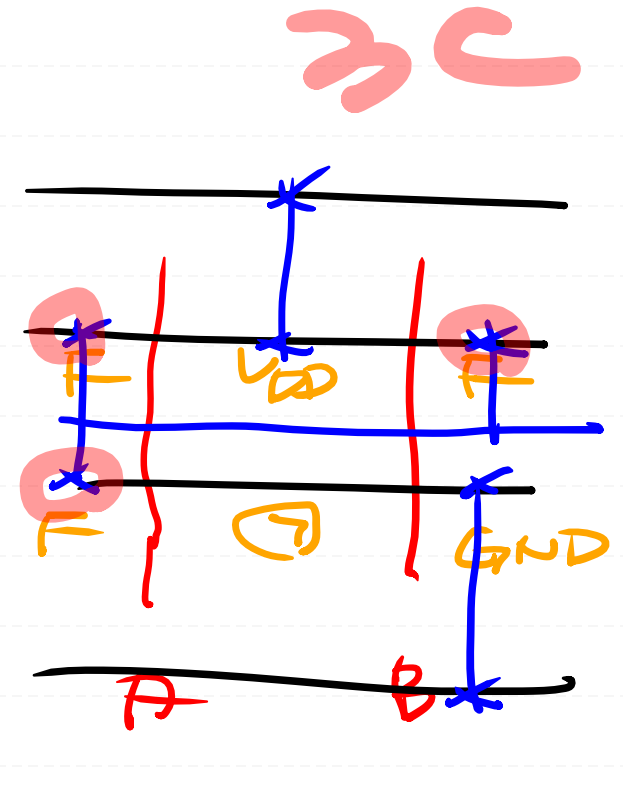
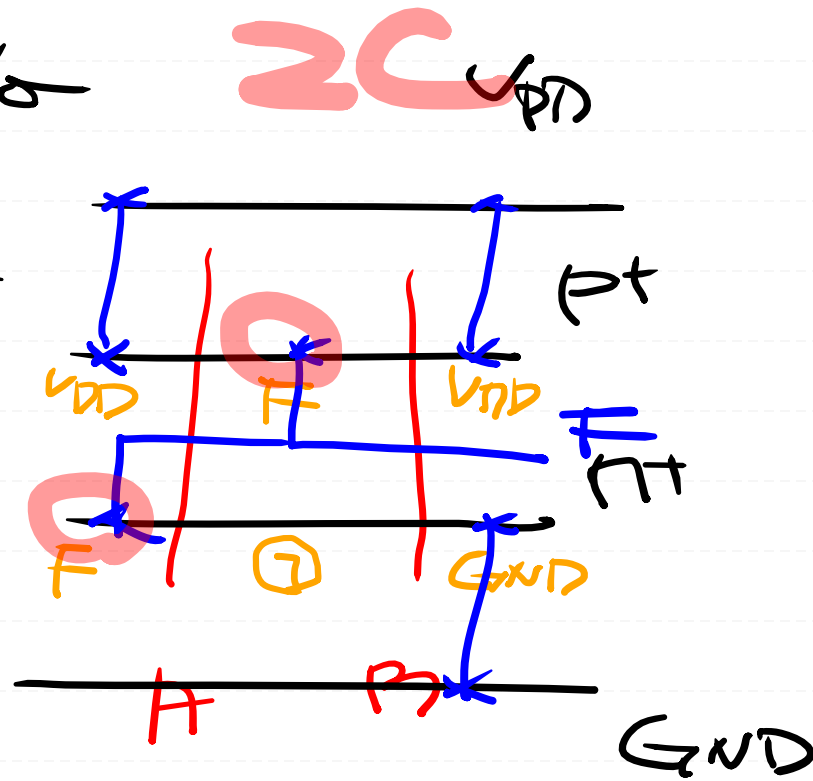
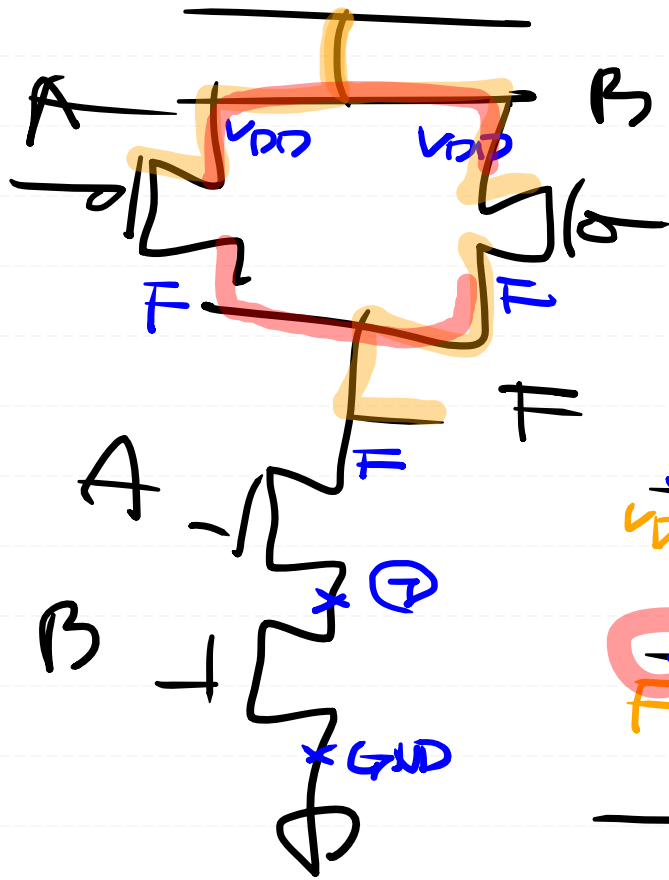


Path !!

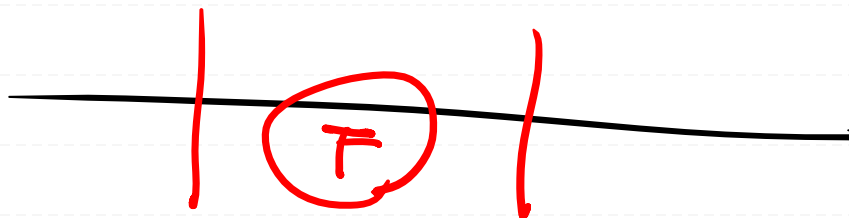
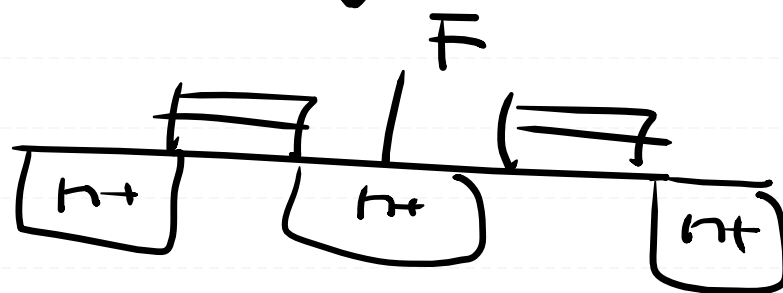
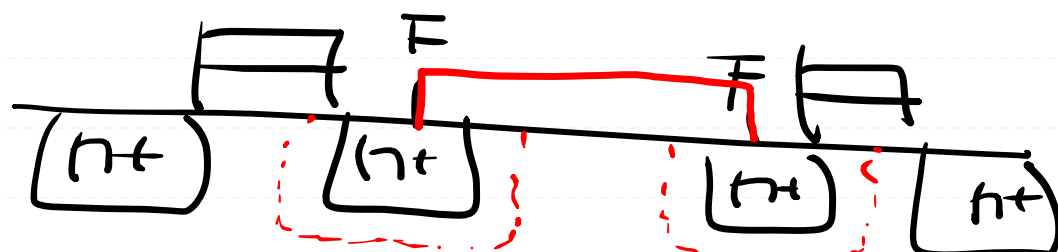
① nmos block 빠른 만큼

② 모든 Tr 낮추기 위해
빠른 게이트.

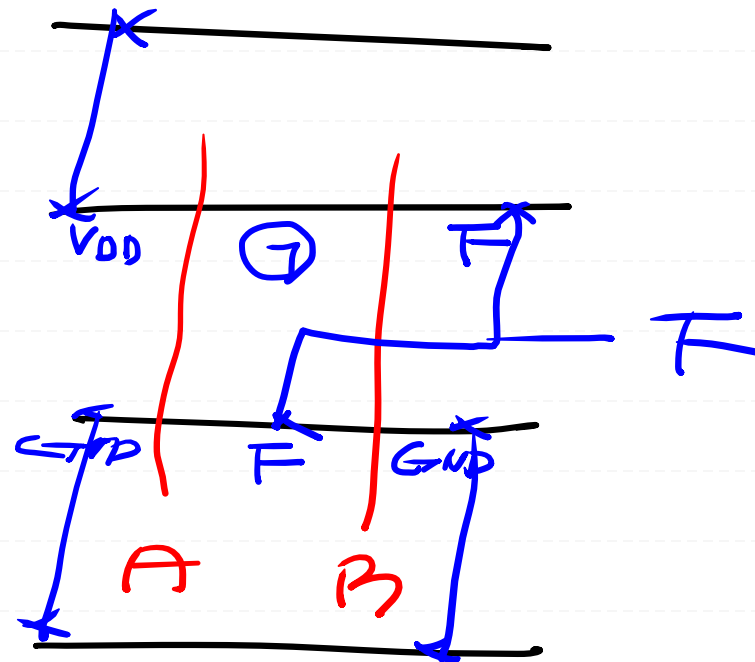
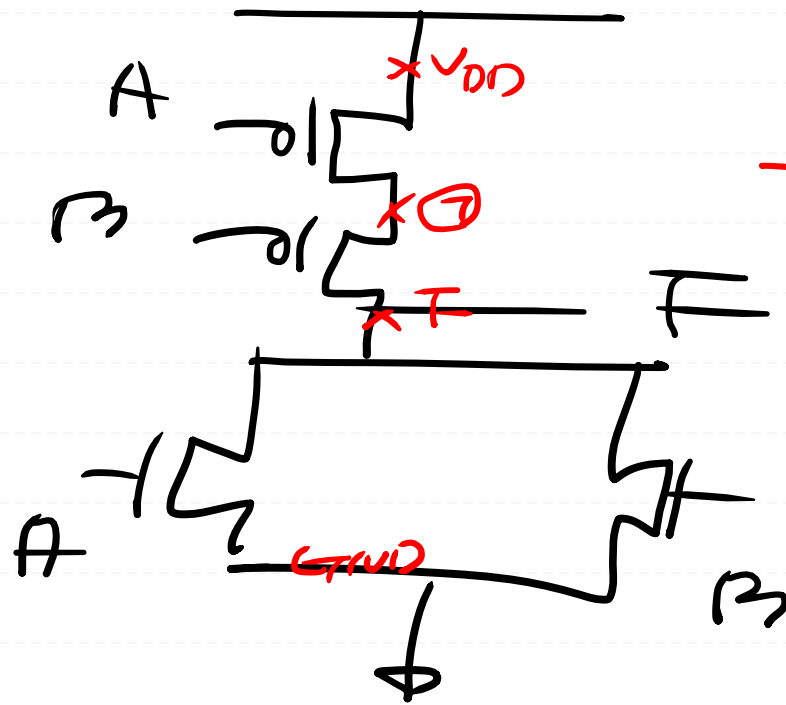
9 $B - A$



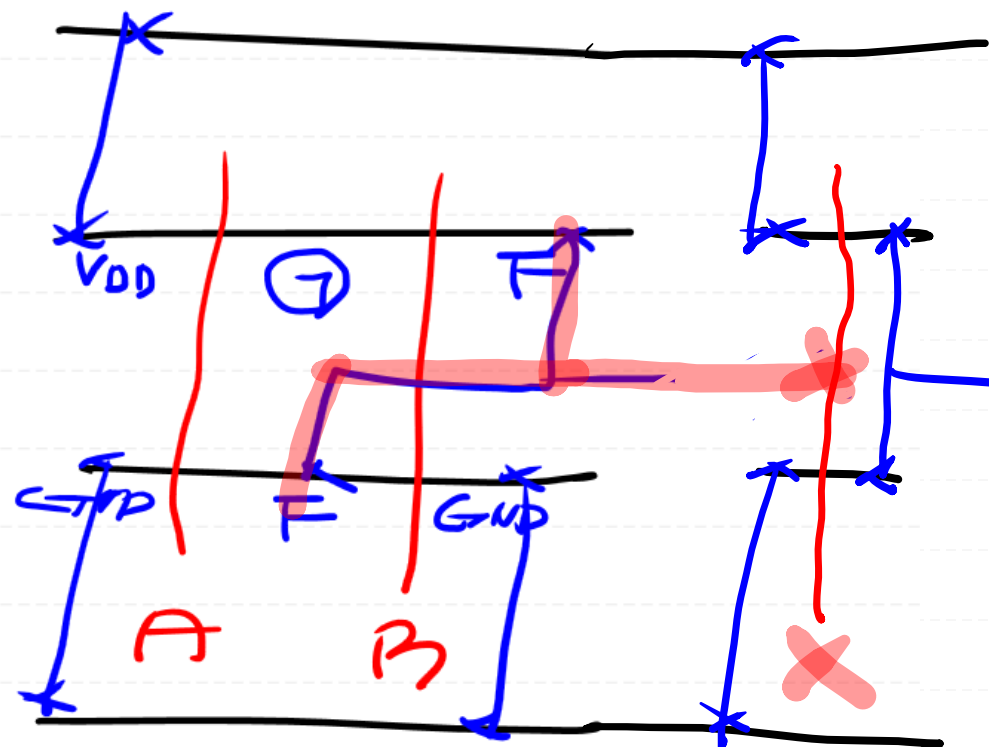
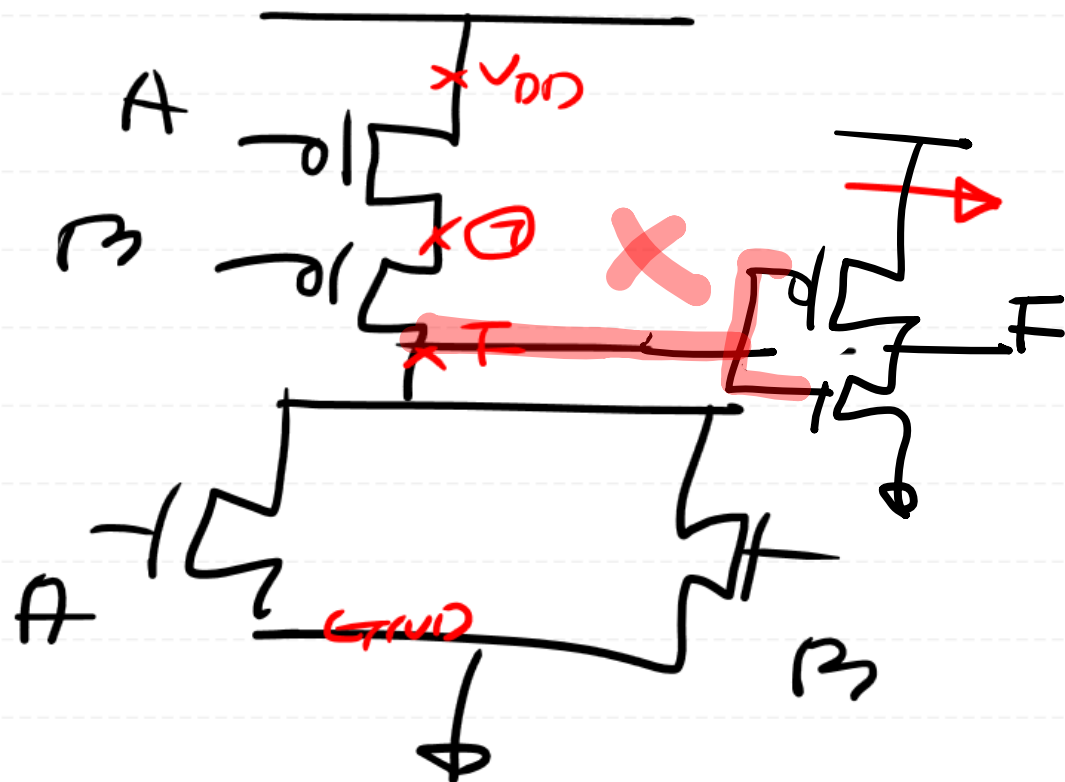
2



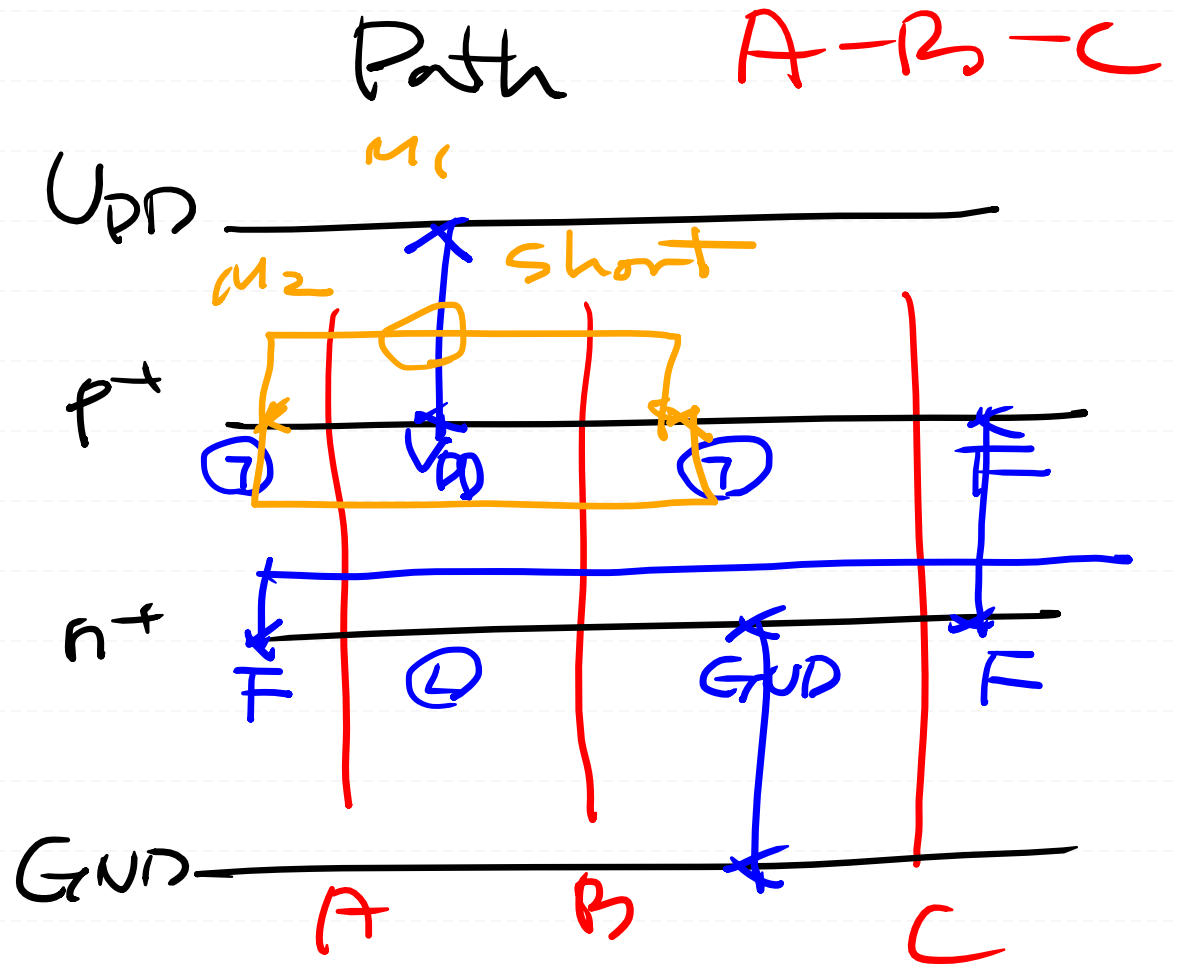
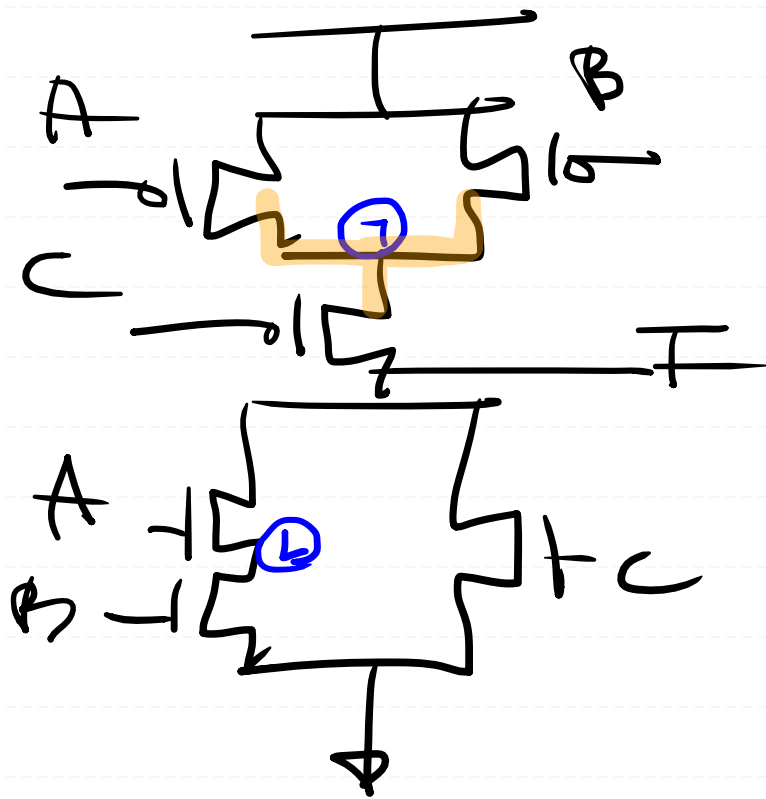
2NOR



OR



$$F = \overline{A \cdot B + C}$$



$\mu_1 \sim \mu_9$

μ_9

$V_{a8} (\mu_9 \sim \mu_8)$

⋮

μ_3

$V_{a2} (\mu_2 + \mu_3)$

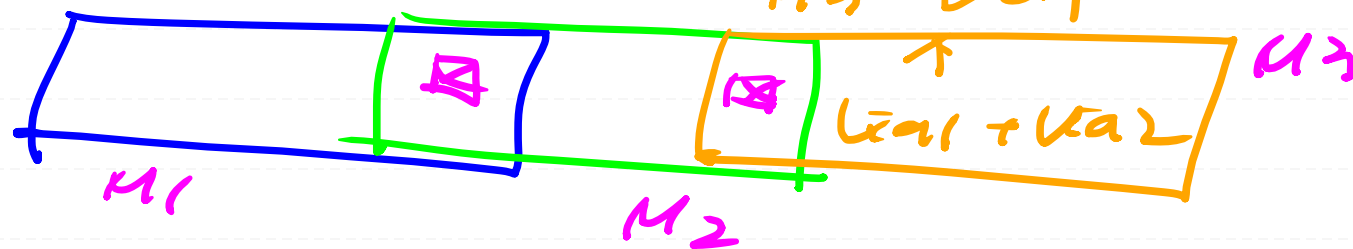
μ_2

$V_{a1} (\mu_1 + \mu_2)$

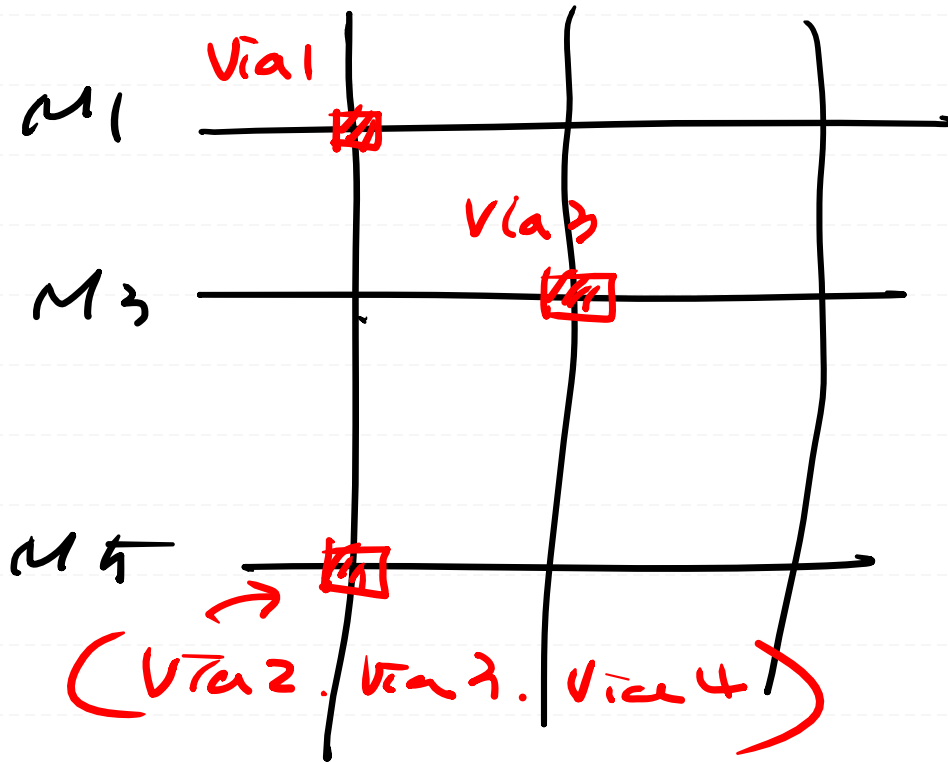
μ_1

V_{a1}

V_{a2}
 $\mu_3 \sim \mu_1$



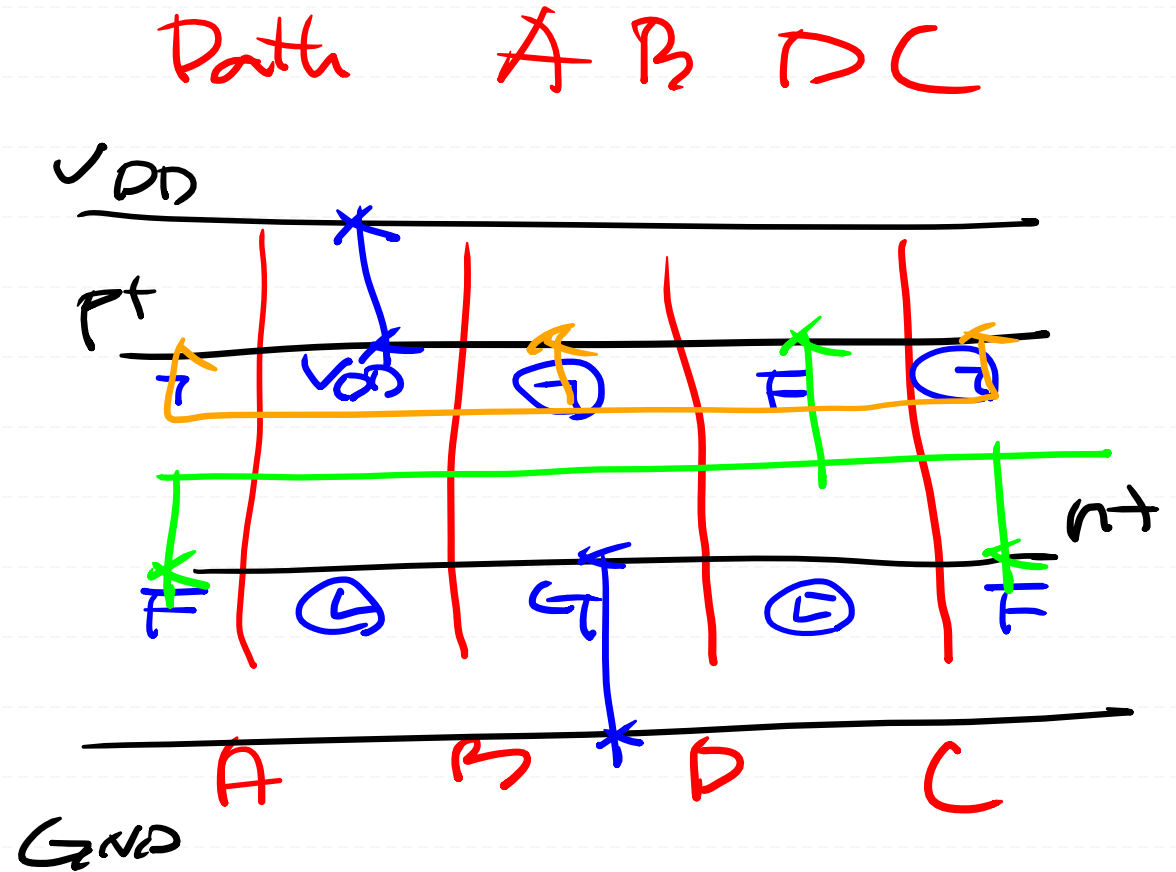
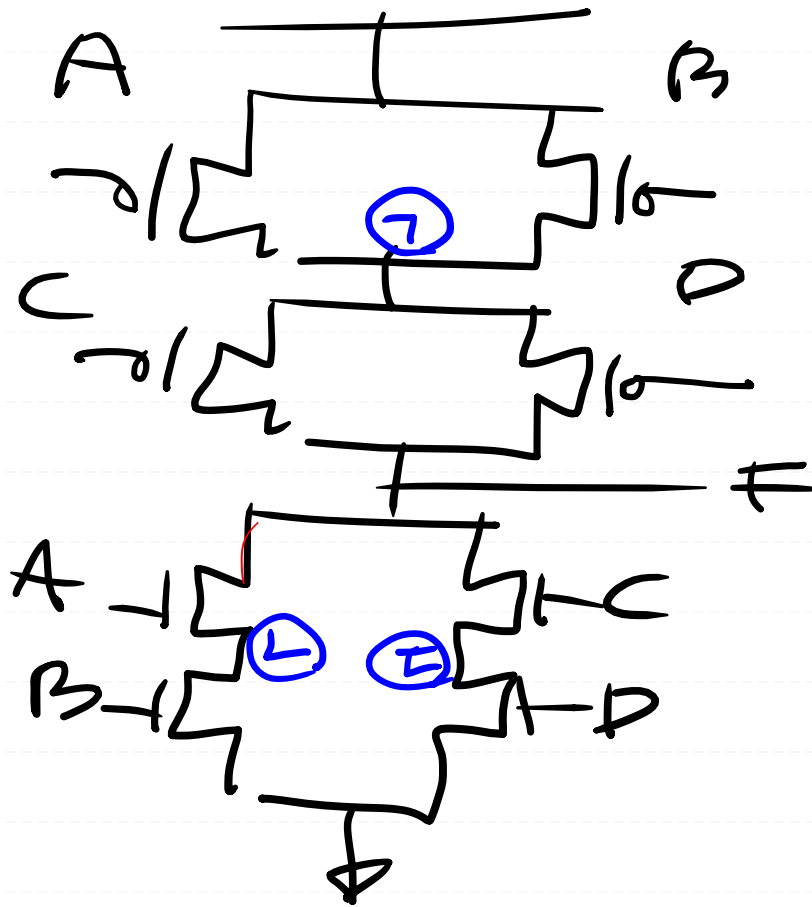
M2 M4 M6



Cap ↓

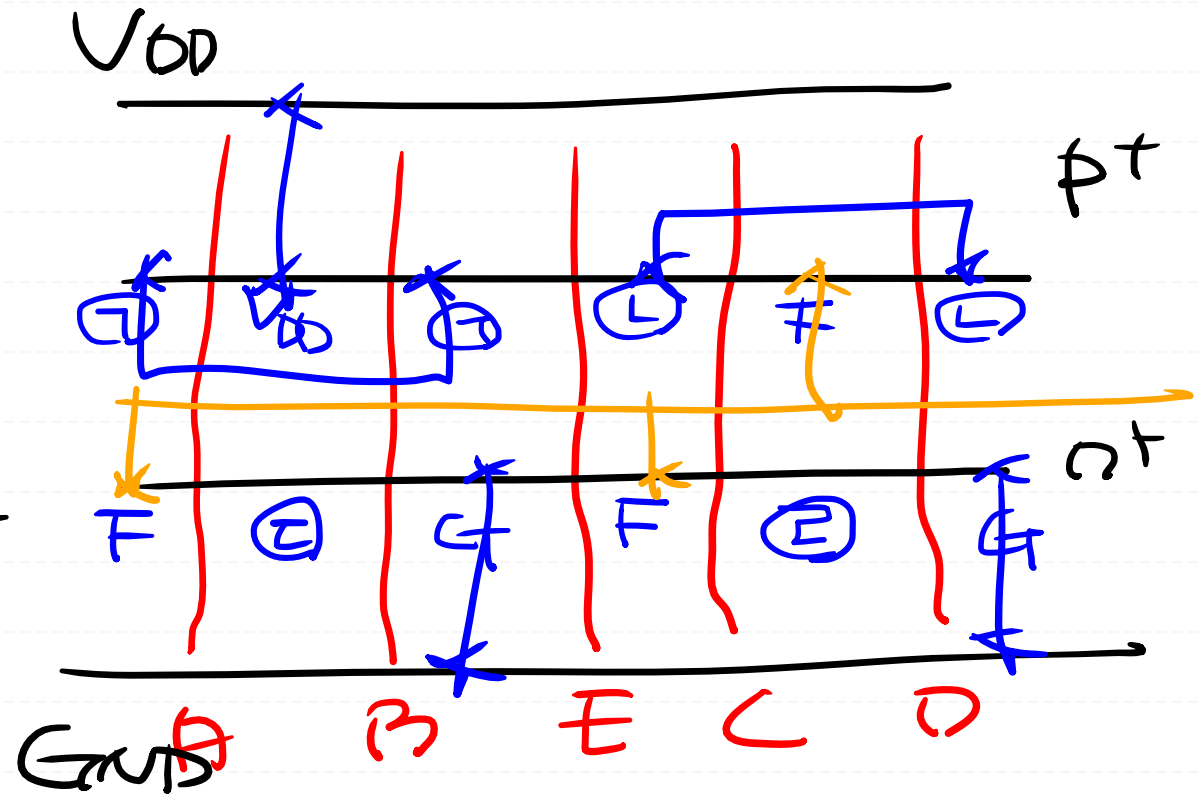
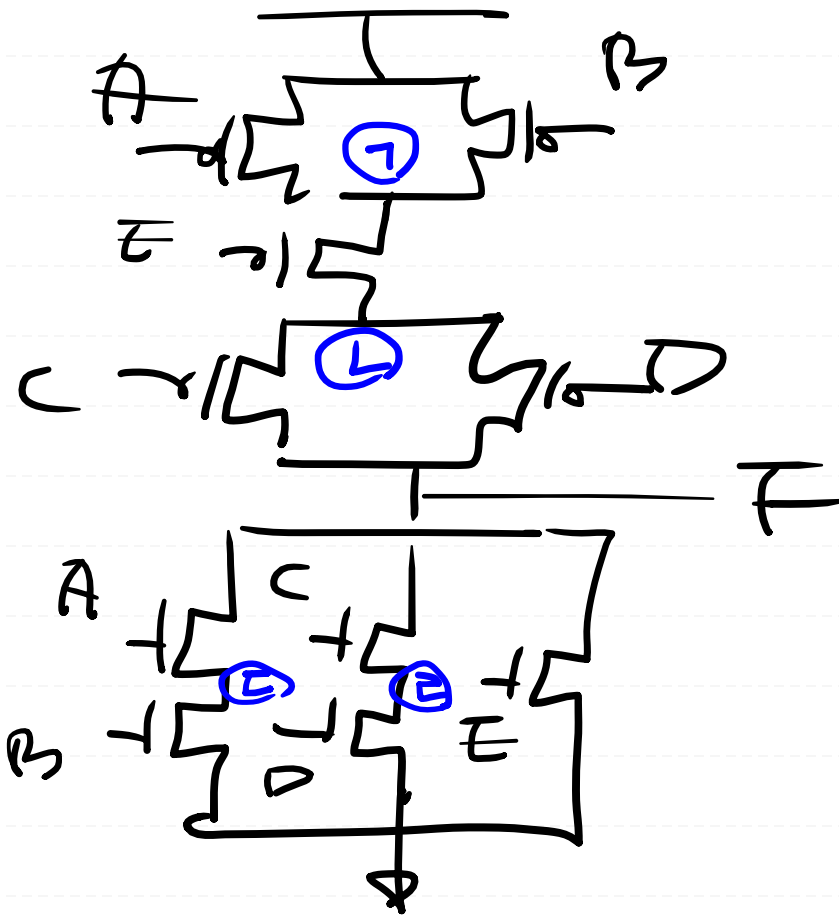
$$F = \overline{A \cdot B + C \cdot D}$$

- ① CMOS schematic
- ② stick Diagram



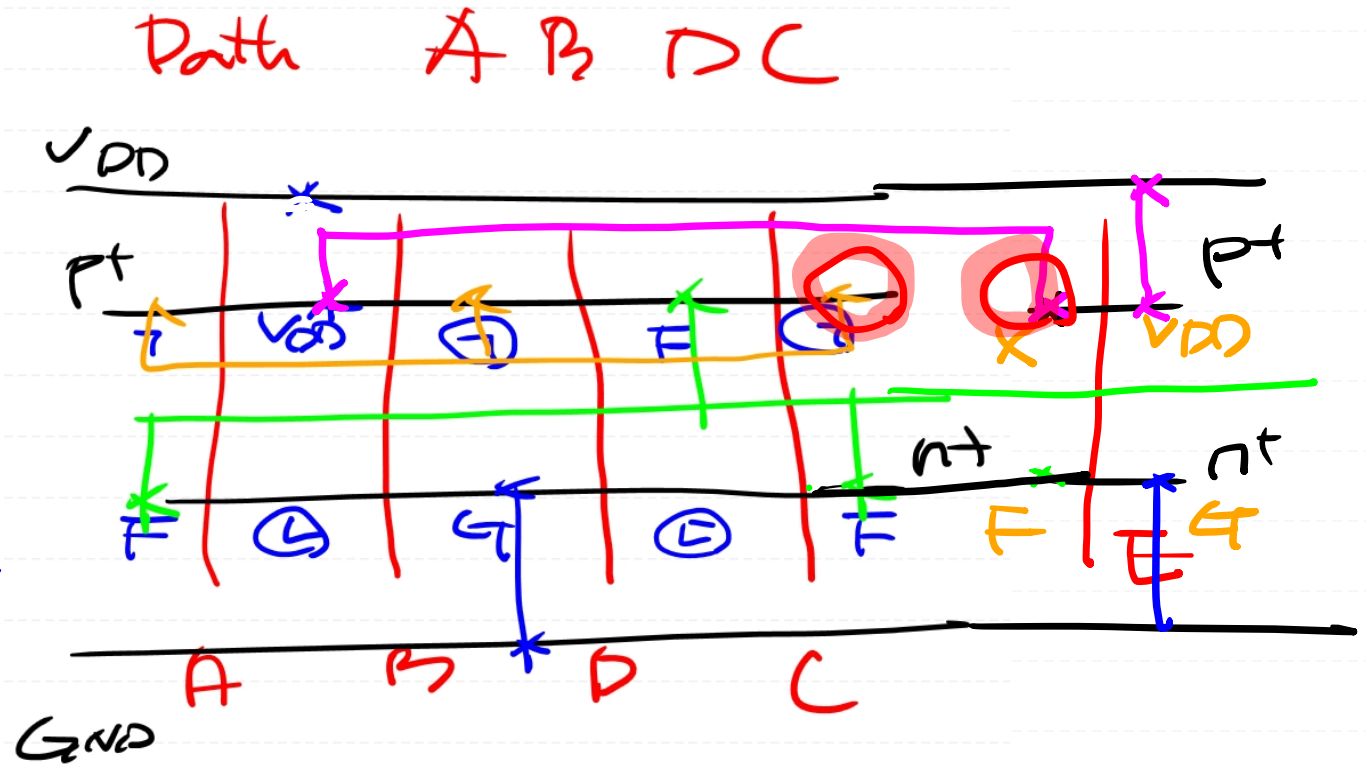
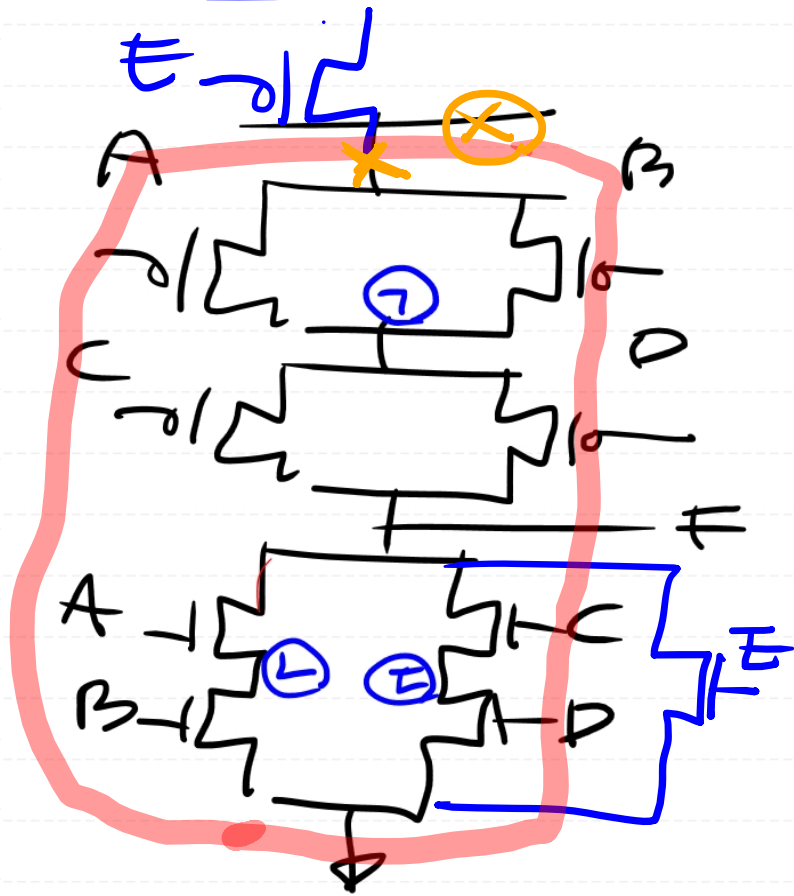
$$F = A \cdot B + C \cdot D + E$$

Path: **A B E C D**



$$F = A \cdot B + C \cdot D + E$$

① CMOS schematic
② stick diagram



$$F = \cancel{A \cdot B} (A + B) = \underline{0 \cdot (A + B)}$$

